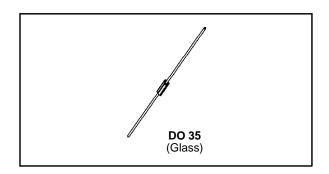


SMALL SIGNAL SCHOTTKY DIODE



Metal to silicon junction diode featuring high breakdown, low turn-on voltage and ultrafast switching. Primarly intended for high level UHF/VHF detection and pulse application with broad dynamic range.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	60	V
l _F	Forward Continuous Current*	15	mA
I _{FSM}	Surge non Repetitive Forward Current*	50	mA
T _{stg} T _j	Storage and Junction Temperature Range	- 65 to 200 - 65 to 200	°C
TL	Maximum Lead Temperature for Soldering dur from Case	230	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
$R_{th(j-a)}$	Junction-ambient*	400	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol		Test Conditions	Min.	Тур.	Max.	Unit
V_{BR}	$T_{amb} = 25^{\circ}C$	$I_R = 10\mu A$	60			>
V _F * *	T _{amb} = 25°C	$I_F = 1 \text{mA}$			0.41	٧
	T _{amb} = 25°C	I _F = 15mA			1	
I _R * *	T _{amb} = 25°C	V _R = 50V			0.2	μΑ

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions				Тур.	Max.	Unit
С	T _{amb} = 25°C	$V_R = 0V$	f = 1MHz			2.2	pF
τ	$T_{amb} = 25^{\circ}C$	$I_F = 5mA$	Krakauer Method			100	ps

^{*} On infinite heatsink with 4mm lead length

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^{**} Pulse test: $t_p \le 300 \mu s \ \delta < 2\%$.

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

Fig.1: Forward current versus forward voltage (typical values).

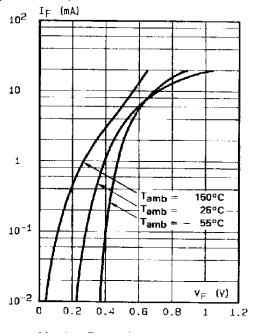


Fig.2: Capacitance C versus reverse applied voltage V_R (typical values).

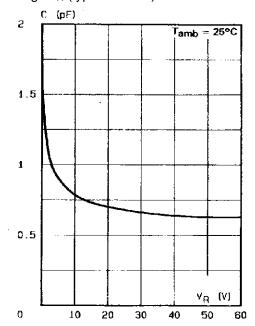


Fig.3: Reverse current versus ambient temperature.

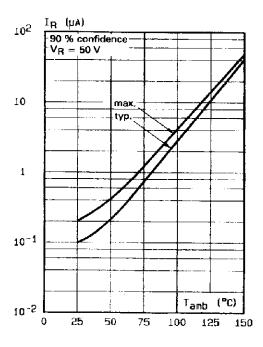
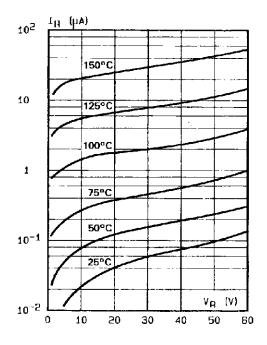
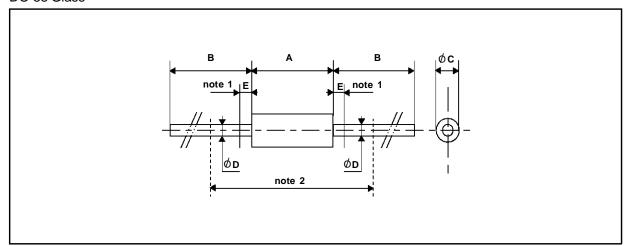


Fig.4: Reverse current versus continuous reverse voltage (typical values).



PACKAGE MECHANICAL DATA

DO 35 Glass



	DIMENSIONS						
REF.	REF. Millimeters		rs Inches		NOTES		
	Min.	Max.	Min.	Max.			
Α	3.050	4.500	0.120	0.117	1 - The lead diameter Ø D is not controlled over zone E		
В	12.7		0.500		The load didinates & Biother controlled ever 20the E		
ØC	1.530	2.000	0.060		2 - The minimum axial lengh within which the device may be		
ØD	0.458	0.558	0.018	0.022	placed with its leads bent at right angles is 0.59"(15 mm)		
Е		1.27		0.050			

Cooling method: by convection and conduction Marking: clear, ring at cathode end. Weight: 0.15g

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